

US009461159B1

(12) **United States Patent**
Chou et al.

(10) **Patent No.:** **US 9,461,159 B1**
(45) **Date of Patent:** **Oct. 4, 2016**

(54) **SELF-STOP GATE RECESS ETCHING
PROCESS FOR SEMICONDUCTOR FIELD
EFFECT TRANSISTORS**

USPC 257/192, 197, 200, 213, 220, 565;
438/142, 156, 167, 172, 173, 182, 212,
438/235, 268, 272

See application file for complete search history.

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(56) **References Cited**

U.S. PATENT DOCUMENTS

5,362,677 A 11/1994 Sakamoto et al.
5,364,816 A 11/1994 Boos et al.

(Continued)

FOREIGN PATENT DOCUMENTS

JP H06-84956 A 3/1994

OTHER PUBLICATIONS

Chang, E. Y. et al. "A GaAs/AlAs Wet Selective Etch Process for the Gate Recess of GaAs Power Metal-Semiconductor Field-Effect Transistors" *Journal of the Electrochemical Society*, 148 (1), 2001, pp. G4-G9.

(Continued)

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(57) **ABSTRACT**

A field effect transistor (FET) device including a GaAs substrate, an AlGaAs buffer layer provided on the substrate, an InGaAs channel layer provided on the buffer layer, an AlGaAs barrier layer provided on the channel layer, a GaAs undoped etch stop layer provided on the barrier layer where the undoped layer defines a depth of a gate recess in the FET device, and a heavily doped GaAs cap layer provided on the etch stop layer. The cap layer has a predetermined thickness and the thickness of the combination of the barrier layer and the undoped layer has the predetermined thickness, where the thickness of the undoped layer and the thickness of the barrier layer are selectively provided relative to each other so as to define the depth of the gate recess.

13 Claims, 3 Drawing Sheets

(21) Appl. No.: **14/996,026**

(22) Filed: **Jan. 14, 2016**

(51) **Int. Cl.**

H01L 21/335 (2006.01)
H01L 21/338 (2006.01)
H01L 21/336 (2006.01)
H01L 29/778 (2006.01)
H01L 29/205 (2006.01)
H01L 29/66 (2006.01)
H01L 21/306 (2006.01)

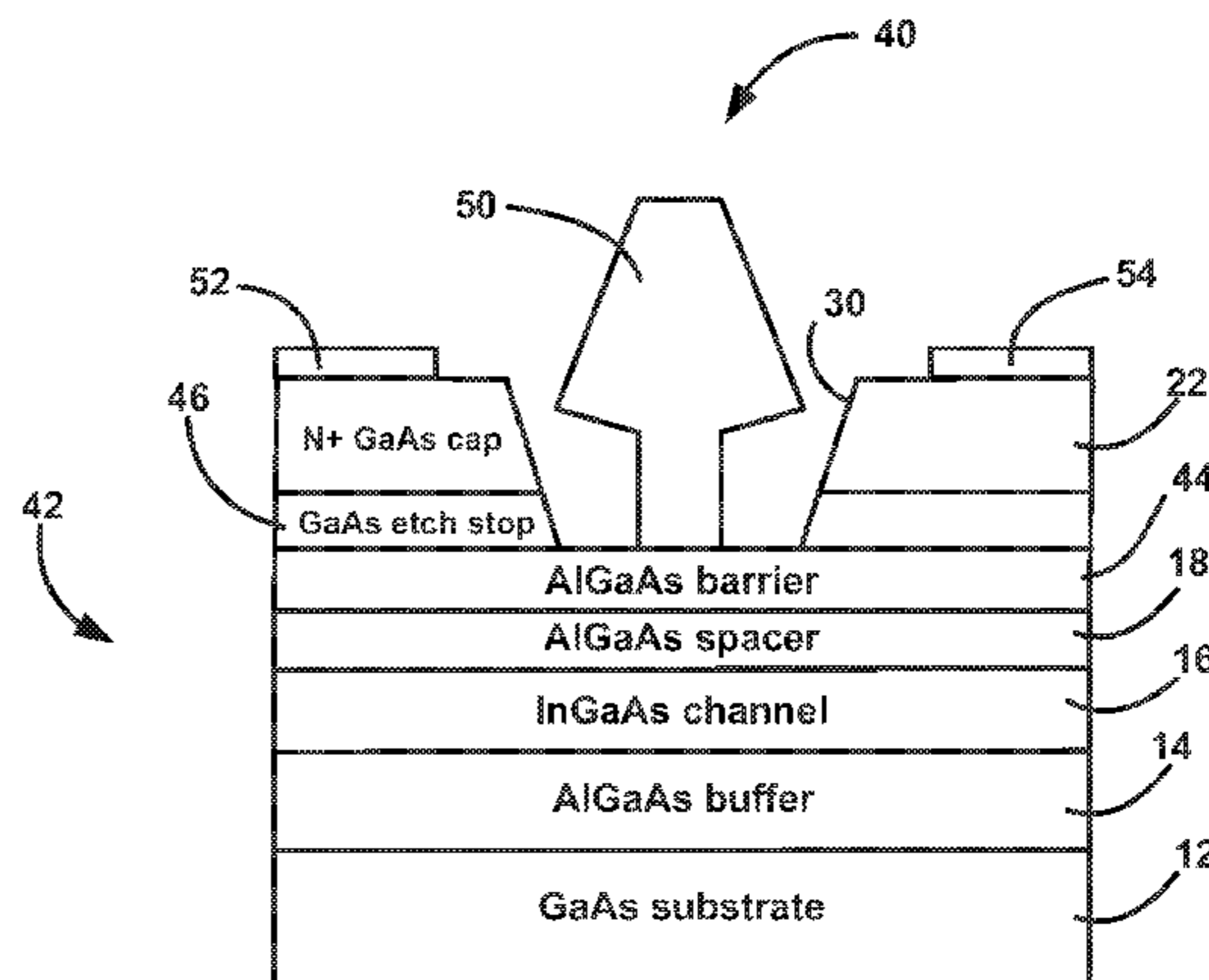
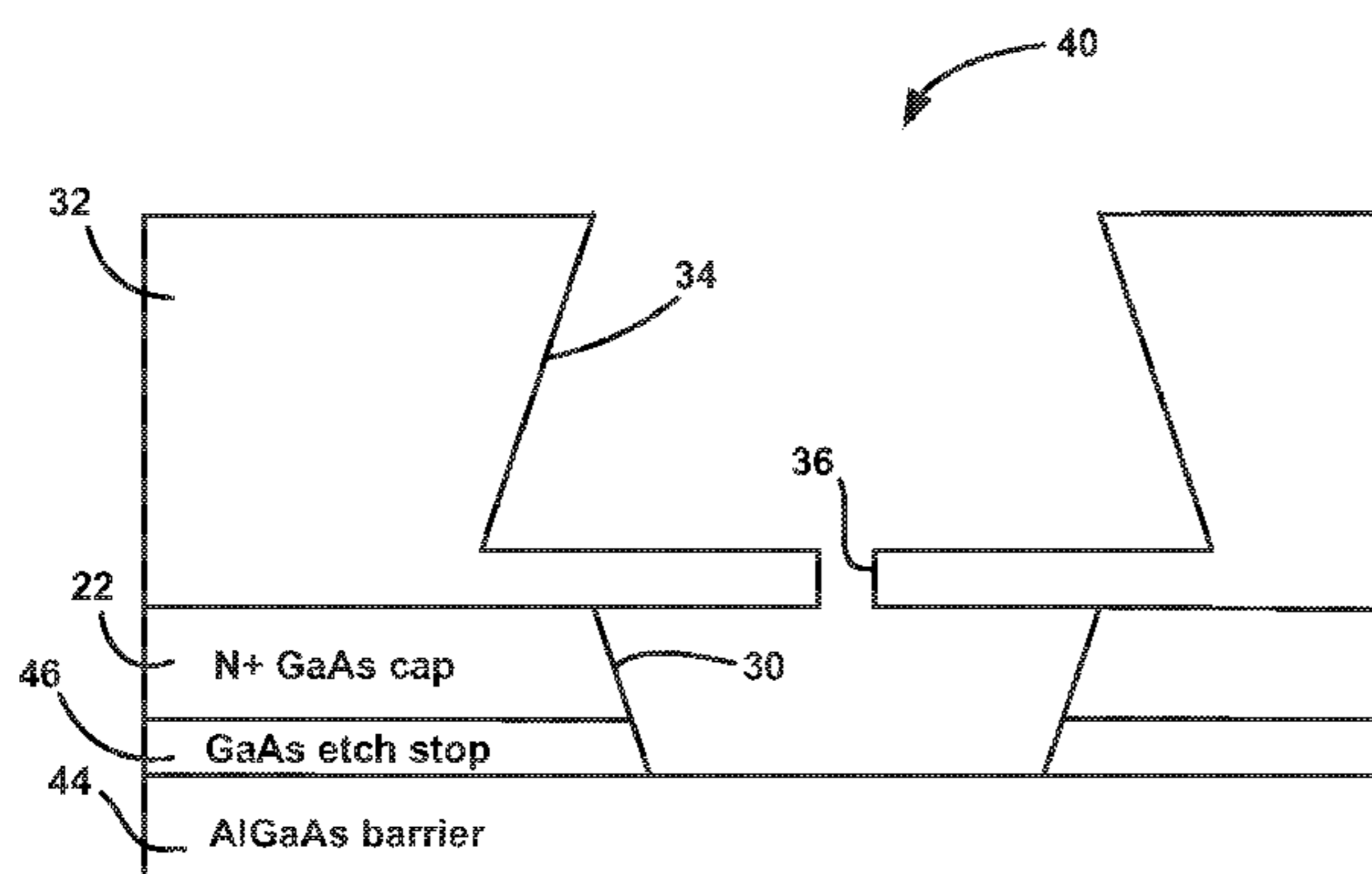
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(52) **U.S. Cl.**

CPC **H01L 29/7784** (2013.01); **H01L 21/02057** (2013.01); **H01L 21/308** (2013.01); **H01L 21/30608** (2013.01); **H01L 29/205** (2013.01); **H01L 29/66462** (2013.01)

(58) **Field of Classification Search**

CPC H01L 29/772; H01L 29/7783; H01L 29/7787; H01L 29/66431; H01L 29/66462; H01L 29/4236; H01L 29/7371; H01L 21/02538; H01L 21/28575



(51) **Int. Cl.**
H01L 21/308 (2006.01)
H01L 21/02 (2006.01)

2006/0043416 A1* 3/2006 P. Li H01L 21/28593
 257/192
 2015/0123171 A1* 5/2015 Radosavljevic H01L 21/2256
 257/194
 2015/0243773 A1* 8/2015 Basu H01L 29/205
 257/194
 2016/0049502 A1* 2/2016 Chin H01L 29/7371
 257/22

(56) **References Cited**

U.S. PATENT DOCUMENTS

5,436,201 A 7/1995 Chi et al.
 5,556,797 A 9/1996 Chi et al.
 5,643,807 A 7/1997 Frijlink et al.
 5,770,525 A 6/1998 Kamiyama
 6,060,402 A 5/2000 Hanson
 6,087,207 A 7/2000 Tong
 6,248,666 B1 6/2001 Frijlink et al.
 6,307,221 B1 10/2001 Danzilio
 6,797,994 B1 9/2004 Hoke et al.
 6,838,325 B2 1/2005 Whelan et al.
 7,199,014 B2 4/2007 Anda
 2003/0080348 A1* 5/2003 Inai H01L 29/7783
 257/192

OTHER PUBLICATIONS

Alavi, K. et al. "A Very High Performance, High Yield, and High Throughput Millimeter Wave Power pHEMT Process Technology" GaAs Mantech, Inc. 2001, 3 pgs.
 Grundbacher, Ronald et al. "Utilization of an Electron Beam Resist Process to Examine the Effects of Asymmetric Gate Recess on the Device Characteristics of AlGaAs/InGaAs PHEMT's" IEEE Transactions on Electron Devices, vol. 44, No. 12, Dec. 1997, pp. 2136-2142.

* cited by examiner

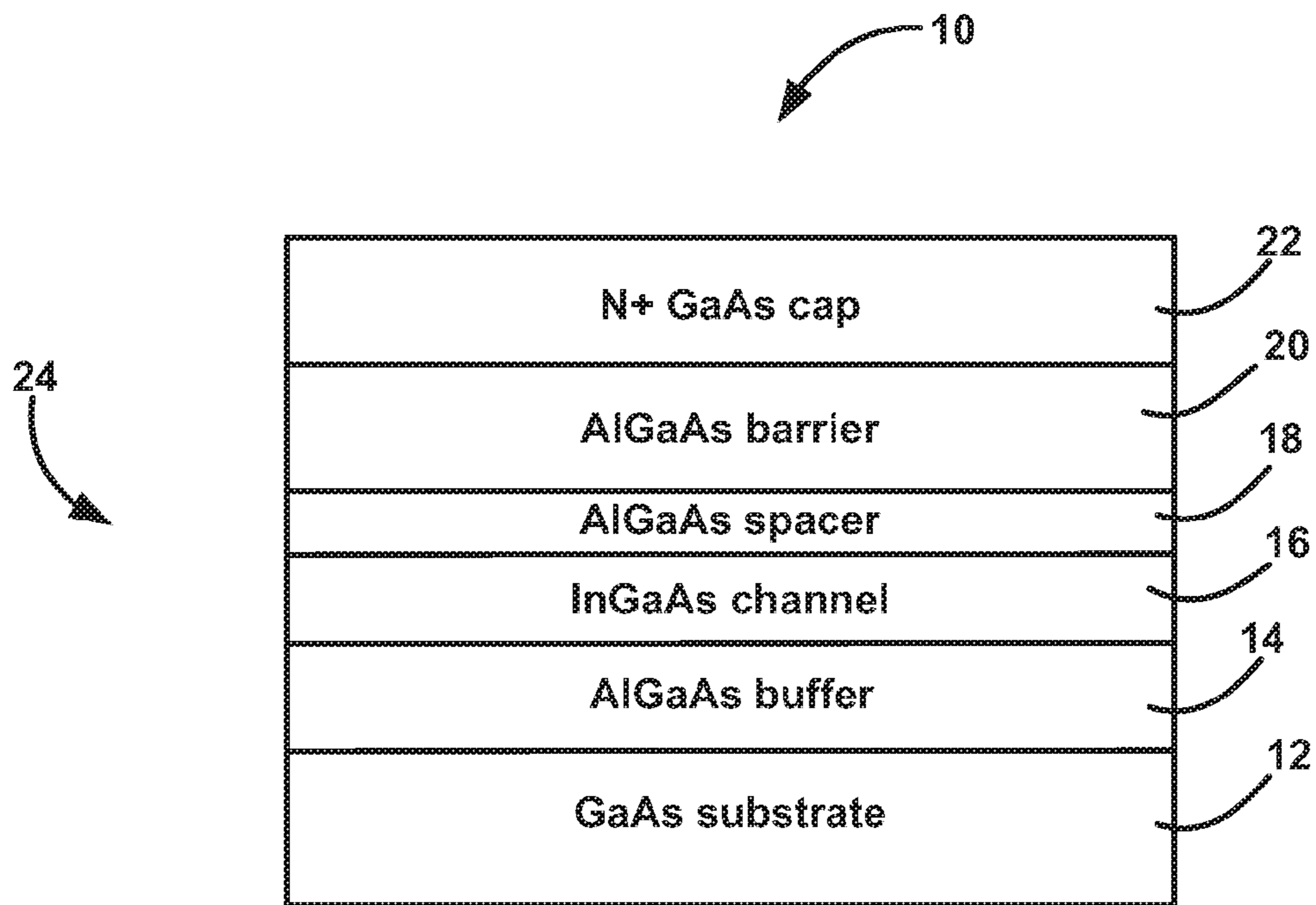


FIGURE 1
(Prior Art)

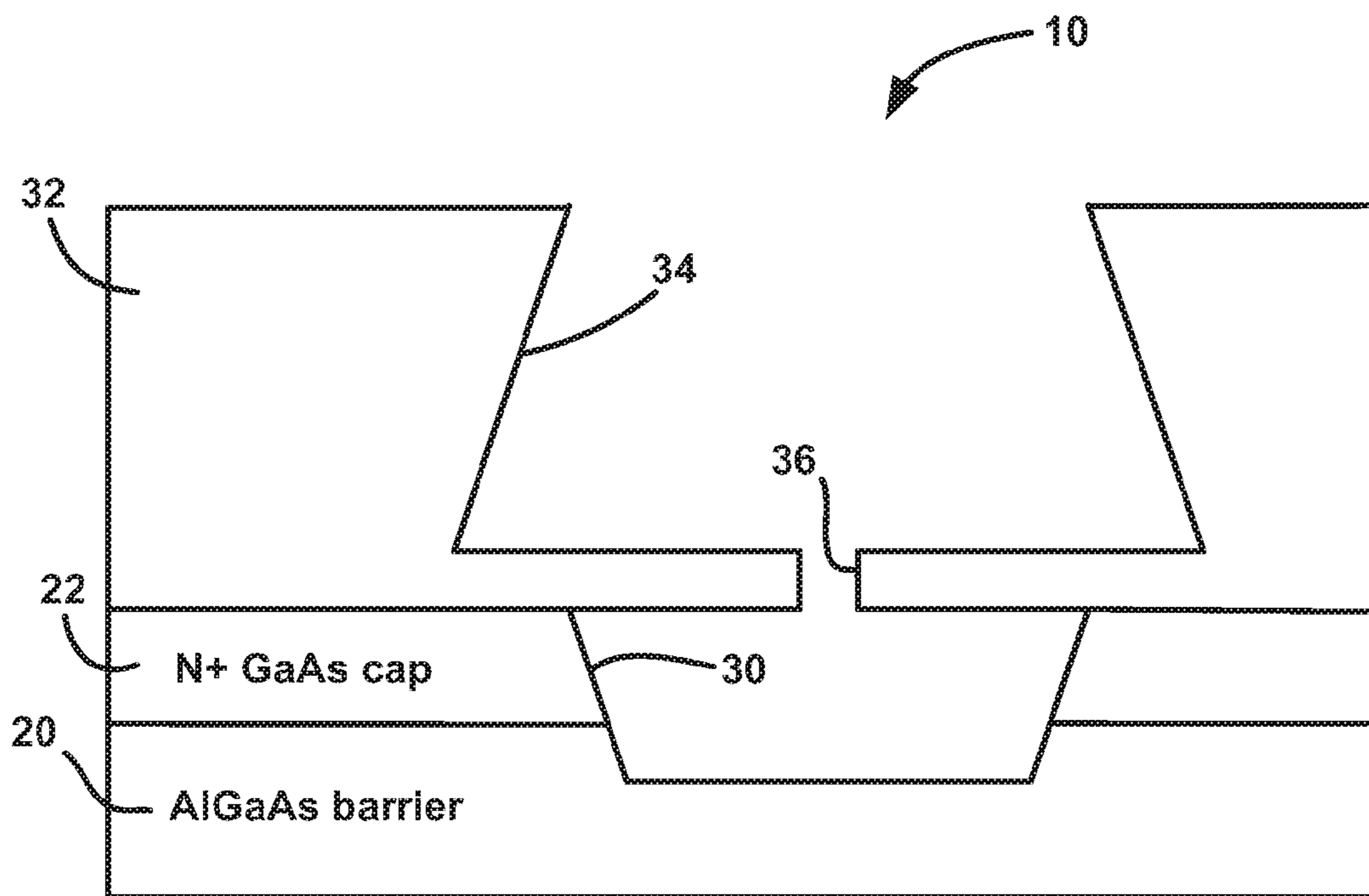


FIGURE 2
(Prior Art)

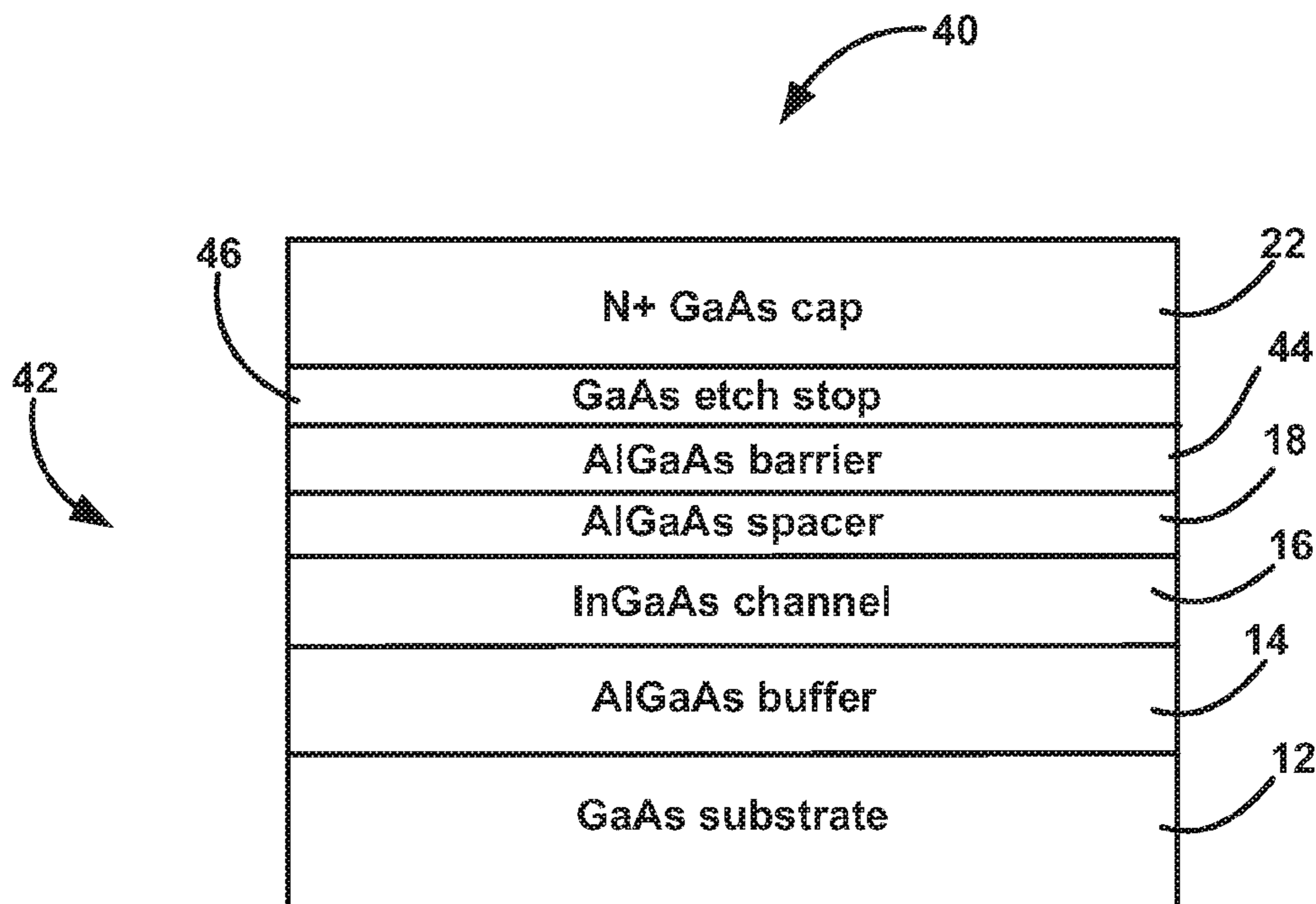


FIGURE 3

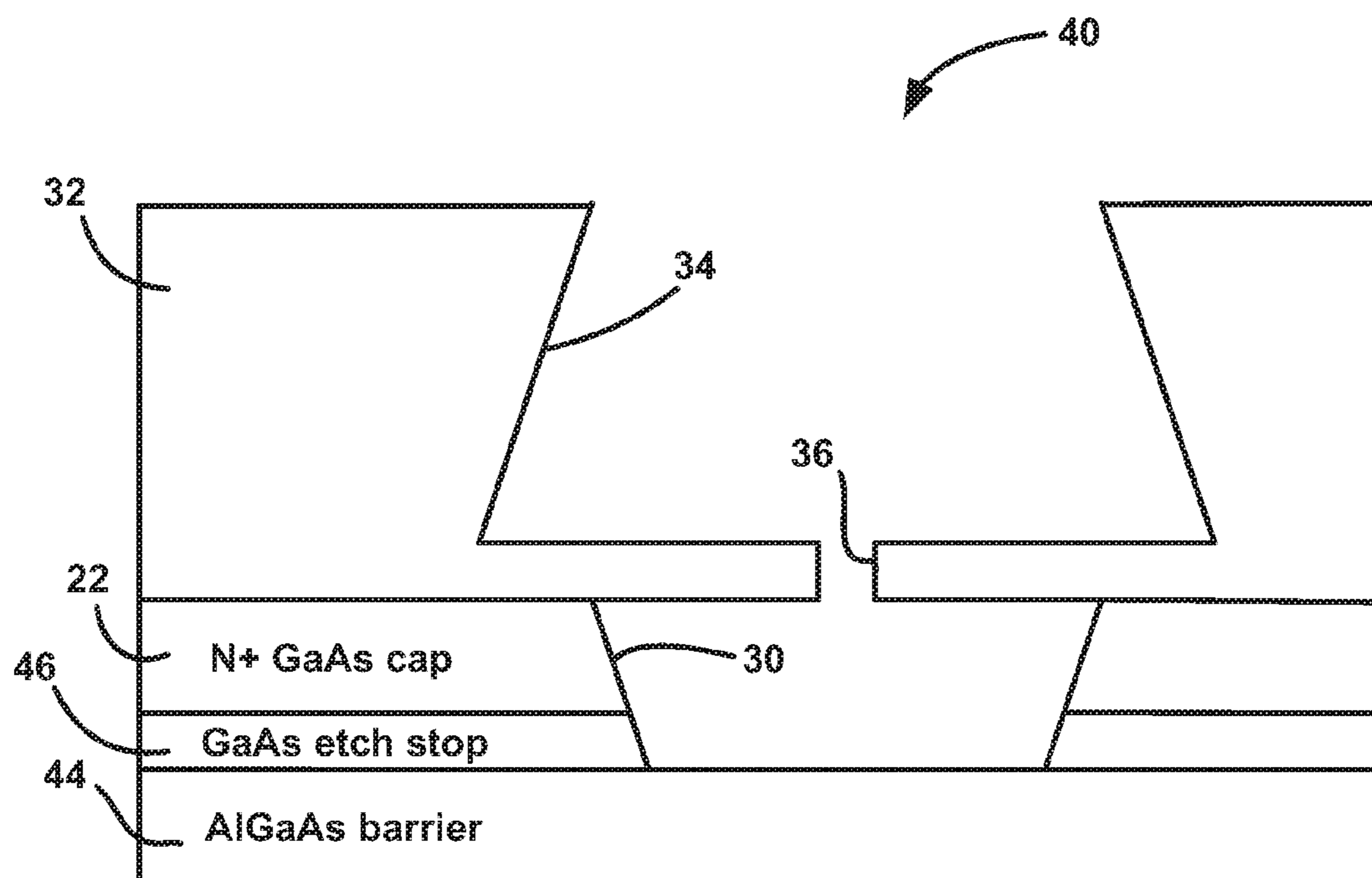


FIGURE 4

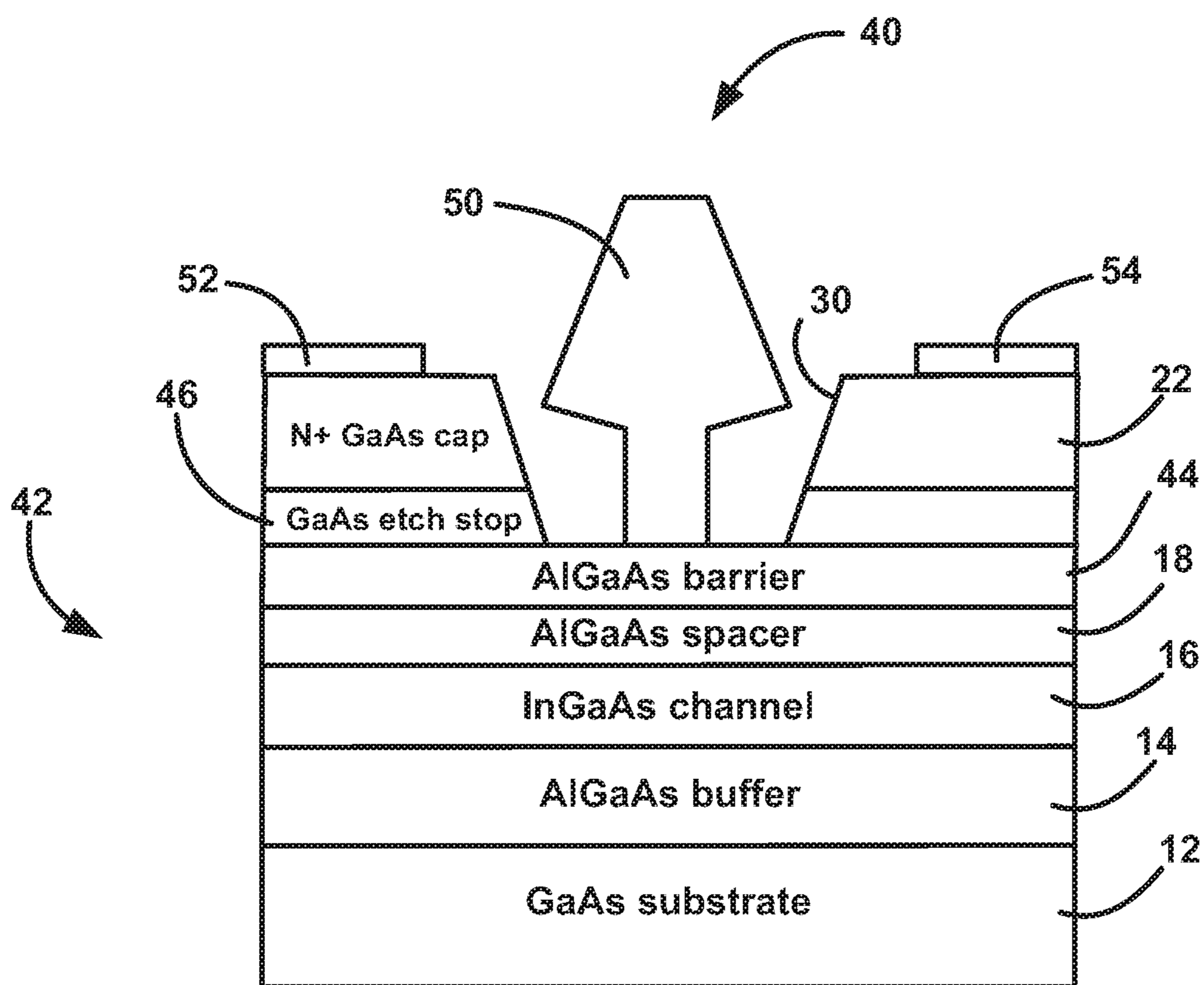


FIGURE 5

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SELF-STOP GATE RECESS ETCHING PROCESS FOR SEMICONDUCTOR FIELD EFFECT TRANSISTORS

BACKGROUND

1. Field

This invention relates generally to a field effect transistor (FET) device including an etch stop layer that defines the etch depth of a gate terminal recess and, more particularly, to an FET device including an etch stop layer that defines the etch depth of a gate terminal recess, where the etch stop layer is an undoped GaAs layer deposited on an AlGaAs barrier layer.

2. Discussion

Field effect transistors (FET) are well known in the transistor art, come in a variety of types, such as HEMT, MOSFET, MISFET, FinFET, etc., and can be integrated as horizontal devices or vertical devices. A typical FET will include various semiconductor layers, such as silicon, gallium arsenide (GaAs), indium gallium arsenide (InGaAs), indium aluminum arsenide (InAlAs), gallium nitride (GaN), indium phosphide (InP), etc. Sometimes the semiconductor layers are doped with various impurities, such as boron or silicon, to increase the population of carriers in the layer, where the higher the doping level of the layer the greater the conductivity of the particular semiconductor material. An FET will also include a source terminal, a drain terminal and a gate terminal, where one or more of the semiconductor layers is a channel layer and is in electrical contact with the source and drain terminals. An electrical potential provided to the source terminal allows electrical carriers, either N-type or P-type, to flow through the channel layer to the drain terminal. An electric signal applied to the gate terminal creates an electrical field that modulates the carriers in the channel layer, where a small change in the gate voltage can cause a large variation in the population of carriers in the channel layer to change the current flow from the source terminal to the drain terminal.

Integrated circuits are typically fabricated by epitaxial fabrication processes that deposit or grow the various semiconductor layers on a semiconductor substrate to provide the circuit components of the device. Substrates for integrated circuits include various semiconductor materials, such as silicon, InP, GaAs, SiC, etc. As integrated circuit fabrication techniques advance and become more complex, more circuit components are able to be fabricated on the substrate within the same area and be more closely spaced together. Further, these integrated circuit fabrication techniques allow the operating frequencies of the circuit to increase to very high frequencies, well into the GHz range.

In a typical FET device, the source terminal and the drain terminal are usually fabricated on a heavily doped cap layer to provide a better conductive path to the channel layer. For certain FET devices, higher performance can be achieved by forming a recess through the cap layer and fabricating the gate terminal in the recess so that it is closer to the channel layer. By placing the gate terminal closer to the channel layer, the transconductance G_m of the device is improved by providing more effective control of the charge in the channel layer, which provides faster switching times.

A typical GaAs FET device includes a heterojunction structure defined by an N+ GaAs cap layer provided on an AlGaAs Schottky barrier layer. A gate recess is formed by first depositing a photoresist layer over the cap layer for all of the devices on the wafer that is patterned to define an opening therein through which the gate recess can be etched

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into the heterojunction structure. A typical gate recess etching process for this type of device generally requires a two-step etching process using two chemical etching solutions, for example, a first etch solution including hydrochloric acid (HCL) and deionized water (DI) and a second etch solution including ammonia (NH_4OH) and hydrogen peroxide (H_2O_2). In one specific example, the two-step etching process includes an initial HCL:DI oxide etch, a deionized water rinse without drying, an initial $\text{NH}_4\text{OH}:\text{H}_2\text{O}_2:\text{DI}$ etch, and then another deionized water. This two-step etching process is repeated over 10-16 cycles to reach the desired depth of the gate recess into the AlGaAs barrier layer.

The gate recess etching process discussed above has a number of drawbacks. For example, the number of two-step etching cycles required makes the process labor intensive and more costly. Further, because of the limitations of the process, the depth of the gate recess etch for a particular FET device on the wafer may not be optimal, and may be different than other gate recess etches of other FET devices on the same wafer, which affects device non-uniformity and performance.

BRIEF DESCRIPTION OF THE DRAWINGS

FIG. 1 is a profile view of a portion of a known GaAs FET device including a heterojunction structure;

FIG. 2 is a profile view of the heterojunction structure shown in FIG. 1 and showing a gate recess formed in a barrier layer of the structure;

FIG. 3 is a profile view of a portion of a GaAs FET device including a homojunction structure;

FIG. 4 is a profile view of the homojunction structure shown in FIG. 3 including an undoped etch stop layer and a gate recess; and

FIG. 5 is a profile view of the GaAs FET device shown in FIG. 3, and including a gate terminal, a source terminal and a drain terminal.

DETAILED DESCRIPTION OF THE EMBODIMENTS

The following discussion of the embodiments of the invention directed to a homojunction structure for a GaAs FET device including an etch stop layer to provide a self-stop gate recess etch is merely exemplary in nature, and is in no way intended to limit the invention or its applications or uses.

FIG. 1 is a profile view of a portion of a known GaAs FET device 10 including a GaAs substrate 12, where the FET device 10 would be one of several FET devices fabricated on a common wafer 24 during the fabrication process. The fabrication process includes depositing an AlGaAs buffer layer 14 on the substrate 12 and depositing an InGaAs channel layer 16 on the buffer layer 14. An AlGaAs spacer layer 18 is deposited on the channel layer 16 and an AlGaAs barrier layer 20 is deposited on the spacer layer 18. A heavily doped N+GaAs cap layer 22 is deposited on the barrier layer 20 and provides electrical contact for source and drain terminals (not shown in FIG. 1). In one embodiment, the barrier layer 20 and the cap layer 22 combine to form a heterojunction structure.

As discussed above, it is desirable to provide a gate terminal (not shown in FIG. 1) close to the channel layer 16. To do this, it is known to provide a gate recess through the cap layer 22 and into the barrier layer 20 in which the gate terminal is deposited. FIG. 2 is a profile view of a portion of the FET 10 showing a gate recess 30 of this type. In order

to define the gate recess **30**, an electron beam lithography (EBL) photoresist layer **32** is deposited on the wafer **24** to a certain thickness, where the photoresist layer **32** can be any suitable resist, such as PMMA, well known to those skilled in the art. Once the photoresist layer **32** is deposited, an electron beam lithography process is performed to provide a wide upper opening **34** and a narrow lower opening **36** in the layer **32** that will ultimately define a T-shape gate terminal. An electron beam is directed onto the wafer **24**, and then the wafer **24** is immersed in a chemical solution to remove material in the photoresist layer **32** to form the openings **34** and **36**.

Once the openings **34** and **36** are formed through the photoresist layer **32** a two-step etching cycling is performed of the type discussed above using the two chemical solutions HCL:DI and NH₄OH:H₂O₂:DI to form the gate recess **30** through the cap layer **22** and into the barrier layer **20**, as shown. It is noted that the etching process undercuts the photoresist layer **32**. A voltage potential applied to the source and drain terminals can be used to monitor the etching process to control the depth and size of the recess **30**. However, as discussed above, multiple two-solution etching cycles are required to achieve the desired etch depth into the barrier layer **20** for the FET devices on the wafer **24**, and thus the etch depth for separate FET devices is not uniform, where different FET devices on the same wafer may have different performances.

The present invention proposes a technique for providing uniformity of the depth of the gate recess for all of the FET devices across the wafer using a single two-solution etching process. FIG. **3** is a profile view of an FET device **40** provided on a wafer **42** similar to the FET device **10**, where like elements are identified by the same reference number. In this embodiment, the barrier layer **20** is replaced with an AlGaAs barrier layer **44** and an undoped GaAs etch stop layer **46** provided between the barrier layer **44** and the cap layer **22**, where the combination of the cap layer **22** and the etch stop layer **46** define a homojunction structure. The thickness of the combination of the barrier layer **44** and the etch stop layer **46** is selected to be the same as the thickness of the barrier layer **20** so that the characteristics of the FET device **40** to that of the FET device **10** does not change.

FIG. **4** is a profile view of the FET device **40**, where like elements to FIG. **2** are shown by the same reference number. In this embodiment, the same chemicals are used in the gate recess etching process, specifically the HCL:DI chemical solution etch and the NH₄OH:H₂O₂:DI chemical solution etch. However, only a single cycle of the two chemical etches is performed, where the etching process automatically stops at a transition between the etch stop layer **46** and the barrier layer **44** because there is a high etching selectivity between GaAs and AlGaAs materials. The etching solutions are selectively provided so that once the etch reaches the AlGaAs barrier layer **44** the etch rate into the layer **44** is very small so that only a minimal amount of the barrier layer **44** is removed. In the known etching process discussed above, the multiple etching cycles allowed the gate recess etch to go into the AlGaAs barrier layer **20**.

The thickness of the layers **44** and **46** is selectively provided to provide the desired depth of the gate recess **30**, where the undoped etch stop layer **46** is made thicker and the barrier layer **44** is made thinner for a deeper recess, and where the thickness of the combination of the layers **44** and **46** is the same regardless of the thickness of the individual undoped layer **46** or the barrier layer **44**.

FIG. **5** is profile view of the FET device **40** after the gate recess **30** has been formed and the photoresist layer **32** has

been removed. Also a gate terminal **50** has been formed in the recess **30**, and a source terminal **52** and a drain terminal **54** have been formed on the cap layer **22** by known fabrication techniques.

The foregoing discussion discloses and describes merely exemplary embodiments of the present invention. One skilled in the art will readily recognize from such discussion and from the accompanying drawings and claims that various changes, modifications and variations can be made therein without departing from the spirit and scope of the invention as defined in the following claims.

What is claimed is:

1. A method for fabricating a field effect transistor (FET) device on a common wafer with other FET devices, said method comprising:

providing a plurality of semiconductor layers including a substrate, a buffer layer deposited on the substrate, a channel layer deposited on the buffer layer, a barrier layer deposited on the channel layer, an undoped etch stop layer deposited on the barrier layer, and a heavily doped cap layer deposited on the undoped etch stop layer;

depositing an electron-beam lithography (EBL) photoresist layer on the semiconductor wafer;

patterning the EBL photoresist layer using an electron-beam lithography process to form a wide an upper opening in the EBL photoresist layer and a narrow lower opening in the EBL photoresist layer where the upper opening is wider than the lower opening;

performing a first etch in a first chemical solution through the upper and lower openings in the EBL photoresist layer and into the wafer for a predetermined period of time; and

performing a second etch in a second chemical solution through the upper and lower openings in the EBL photoresist layer for a predetermined period of time to form a gate recess to a depth defined by a transition between the undoped etch stop layer and the barrier layer.

2. The method according to claim **1** wherein the first chemical solution is HCL:DI and the second chemical solution is NH₄OH:H₂O₂:DI.

3. The method according to claim **1** further comprising rinsing the wafer in deionized water between the first and second etches and after the second etch.

4. The method according to claim **1** wherein providing a plurality of semiconductor layers includes providing a GaAs substrate, an AlGaAs buffer layer, an InGaAs channel layer, an AlGaAs barrier layer, a GaAs etch stop layer and a GaAs cap layer.

5. The method according to claim **1** wherein providing a plurality of semiconductor layers includes providing the heavily doped cap layer to have a predetermined thickness and providing the barrier layer and the undoped etch stop layer to have a combined thickness the same as the predetermined thickness.

6. The method according to claim **5** wherein providing a plurality of semiconductor layers includes selectively defining a thickness of the undoped etch stop layer and a thickness of the barrier layer so as to define the depth of the gate recess.

7. A method for fabricating a field effect transistor (FET) device on a common wafer with other FET devices, said method comprising:

providing a plurality of semiconductor layers including a substrate, a buffer layer deposited on the substrate, a channel layer deposited on the buffer layer, a barrier

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layer deposited on the channel layer, an undoped etch stop layer deposited on the barrier layer, and a heavily doped cap layer deposited on the undoped etch stop layer;

depositing an electron-beam lithography (EBL) photoresist layer on the semiconductor wafer;

patterning the EBL photoresist layer using an electron-beam lithography process to form an upper opening in the EBL photoresist layer and a lower opening in the EBL photoresist layer where the upper opening is wider than the lower opening;

performing a first etch in an HCLDI chemical solution through the upper and lower openings in the EBL photoresist layer and into the wafer;

performing a second etch in an NH₄OH:H₂O₂:DI chemical solution through the upper and lower openings in the EBL photoresist layer to form a gate recess to a depth defined by a transition between the etch stop layer and the barrier layer; and

rinsing the wafer in deionized water between the first and second etches and after the second etch.

8. The method according to claim 7 wherein providing a plurality of semiconductor layers includes providing a GaAs substrate, an AlGaAs buffer layer, an InGaAs channel layer, an AlGaAs barrier layer, a GaAs etch stop layer and a GaAs cap layer.

9. The method according to claim 7 wherein providing a plurality of semiconductor layers includes providing the heavily doped cap layer to have a thickness and providing the barrier layer and the undoped etch stop layer to have a combined thickness the same as the thickness.

10. The method according to claim 9 wherein providing a plurality of semiconductor layers includes selectively defining a thickness of the undoped etch stop layer and a thickness of the barrier layer so as to define the depth of the gate recess.

11. A method for fabricating a field effect transistor (FET) device on a common wafer with other FET devices, said method comprising:

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providing a plurality of semiconductor layers including a GaAs substrate, an AlGaAs buffer layer deposited on the substrate, an InGaAs channel layer deposited on the buffer layer, an AlGaAs barrier layer deposited on the InGaAs channel layer, an undoped GaAs etch stop layer deposited on the barrier layer, and a heavily doped GaAs cap layer deposited on the undoped GaAs etch stop layer, wherein providing a plurality of semiconductor layers includes providing the heavily doped GaAs cap layer to have a thickness and providing the barrier layer and the undoped GaAs etch stop layer to have a combined thickness the same as the thickness; depositing an electron-beam lithography (EBL) photoresist layer on the semiconductor wafer;

patterning the EBL photoresist layer using an electron-beam lithography process to form an upper opening in the EBL photoresist layer and a lower opening in the EBL photoresist layer where the upper opening is wider than the lower opening;

performing a first etch in a first chemical solution through the upper and lower openings in the EBL photoresist layer and into the wafer; and

performing a second etch in a second chemical solution through the upper and lower openings in the EBL photoresist layer to form a gate recess to a depth defined by a transition between the undoped GaAs etch stop layer and the AlGaAs barrier layer, wherein providing a plurality of semiconductor layers includes selectively defining a thickness of the undoped etch stop layer and a thickness of the AlGaAs barrier layer so as to define the depth of the gate recess.

12. The method according to claim 11 wherein the first chemical solution is HCL:DI and the second chemical solution is NH₄OH:H₂O₂:DI.

13. The method according to claim 11 further comprising rinsing the wafer in deionized water between the first and second etches and after the second etch.

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